

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0008] as follows:

[0008] In FIG. 3B, an insulating[[nsulating]] material is deposited on an entire surface of the lower substrate 1 for covering the gate line 2 and the gate electrode 6, thereby forming a gate insulating film 12. First and second semiconductor materials are sequentially deposited on the gate insulating film 12, and subsequently patterned, thereby forming an active layer 14 and an ohmic contact[[contract]] layer 16.